

B1  
concl'd  
C1

layer.

B2

97. (amended) A capacitor for a semiconductor device, said capacitor comprising:

a tungsten nitride bottom layer;

a tantalum pentoxide layer formed over said tungsten nitride bottom layer; and

an annealed platinum layer formed over said tantalum pentoxide layer.

sub  
C3

98. (amended) A capacitor for a semiconductor device, said capacitor comprising:

a bottom conducting layer;

a dielectric layer formed over said bottom conducting layer; and

an annealed top conducting layer formed over said dielectric layer, wherein each of said bottom and annealed top conducting layers is formed of a material selected from the group consisting of platinum, platinum rhodium, platinum iridium, and tungsten nitride.